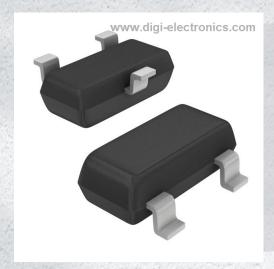


# **MMBTA63LT1G Datasheet**



https://www.DiGi-Electronics.com

DiGi Electronics Part Number MMBTA63LT1G-DG

Manufacturer onsemi

Manufacturer Product Number MMBTA63LT1G

Description TRANS PNP DARL 30V 0.5A SOT23-3

Detailed Description

Bipolar (BJT) Transistor PNP - Darlington 30 V 500 m

A 125MHz 225 mW Surface Mount SOT-23-3 (TO-23

)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
MMBTA63LT1G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP - Darlington	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
30 V	1.5V @ 100μA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	5000 @ 100mA, 5V
Power - Max:	Frequency - Transition:
225 mW	125MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	SOT-23-3 (TO-236)
Base Product Number:	
MMBTA63	

# **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0075	





# **Darlington Transistors**

### **PNP Silicon**

# MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G,

#### **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CES</sub>	-30	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-30	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-10	Vdc
Collector Current - Continuous	Ic	-500	mAdc

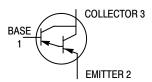
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2)  T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.





#### **MARKING DIAGRAM**



2x = Device Code

x = U for MMBTA63LT1G x = V for MMBTA64LT1G SMMBTA64LT1G

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBTA63LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA64LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA64LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G,

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	•
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = –100 µAdc)	V <sub>(BR)</sub> CEO	-30	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = -30 Vdc)	Ісво	-	-100	nAdc
Emitter Cutoff Current (V <sub>EB</sub> = -10 Vdc)	I <sub>EBO</sub>	-	-100	nAdc
ON CHARACTERISTICS	·			
DC Current Gain (Note 3) $ \begin{aligned} &(I_C=-10 \text{ mAdc, V}_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA63} \\ &(I_C=-10 \text{ mAdc, V}_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA64, SMMBTA64} \\ &(I_C=-100 \text{ mAdc, V}_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA63} \\ &(I_C=-100 \text{ mAdc, V}_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA64, SMMBTA64} \end{aligned} $	h <sub>FE</sub>	5,000 10,000 10,000 20,000		-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = -100 mAdc, I <sub>B</sub> = -0.1 mAdc)	V <sub>CE(sat)</sub>	-	-1.5	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = –100 mAdc, V <sub>CE</sub> = –5.0 Vdc)	V <sub>BE(on)</sub>	-	-2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS	·			
Current – Gain – Bandwidth Product (I <sub>C</sub> = -10 mAdc, V <sub>CE</sub> = -5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	125	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

### MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G,

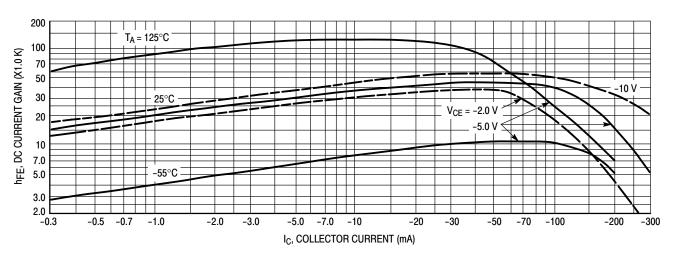


Figure 1. DC Current Gain

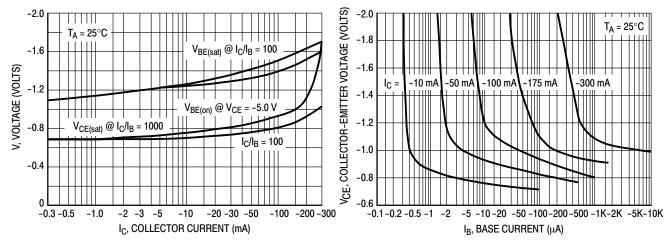


Figure 3. "On" Voltage

IhFEI, HIGH FREQUENCY CURRENT GAIN

4.0

3.0 2.0

1.0

0.4

V<sub>CE</sub> = -5.0 V f = 100 MHz

\_ T<sub>A</sub> = 25°C

-2.0

-1.0

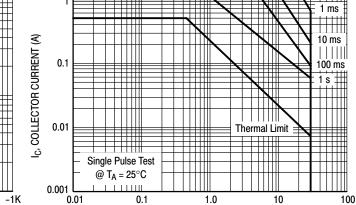


Figure 2. Collector Saturation Region

-500

IC, COLLECTOR CURRENT (mA) Figure 4. High Frequency Current Gain

-50 -100 -200

-20

V<sub>CE</sub>, COLLECTOR-EMITTER VOLTAGE (V) Figure 5. Safe Operating Area



# **MECHANICAL CASE OUTLINE**

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

\_\_\_

# PACKAGE DIMENSIONS



#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

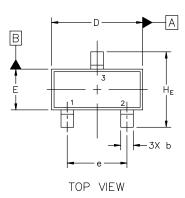
2.04

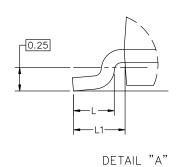
0.55

0.69

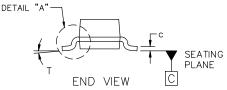
2.64

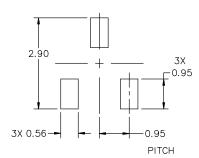
10°











Scale 3:1

## NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1.
- PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

### **GENERIC MARKING DIAGRAM\***

SIDE VIEW



XXX = Specific Device Code

= Date Code

= Pb-Free Package

#### RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7:         STYLE 8:           PIN 1. EMITTER         PIN 1. ANOD           2. BASE         2. NO CC           3. COLLECTOR         3. CATHO	ONNECTION	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11:         STYLE 12:           PIN 1.         ANODE         PIN 1.         CATHO           2.         CATHODE         2.         CATHO           3.         CATHODE-ANODE         3.         ANODO	ODE 2. DRAIN 2. GATE	
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17:         STYLE 18:           PIN 1. NO CONNECTION         PIN 1. NO CO           2. ANODE         2. CATHO           3. CATHODE         3. ANODO	ODE 2. ANODE 2. ANODE	
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23:         STYLE 24:           PIN 1. ANODE         PIN 1. GATE           2. ANODE         2. DRAIN           3. CATHODE         3. SOURCE		CTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

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